



PCN# : P574AAB
Issue Date : Jul. 20, 2015

Information Only Notification

This is to inform you that a change is being made to the following products.

This is a minor change that has no impact on product quality, reliability, electrical or mechanical performance. Affected products will remain fully compliant to all published specifications. Notification is being made for informational purposes only and there is no approval required. Products incorporating this change may be shipped interchangeably with existing unchanged products.

Please contact your local Customer Quality Engineer if you have any questions regarding this notification. Alternatively, you may send an email request for information to PCNSupport@fairchildsemi.com.

Implementation of change:

Description of Change (From) :
Datasheet Description for Product on Page 1

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. In addition, internal gate-source ESD diode allows to withstand over 2kV HBM surge stress. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as Audio, Laptop adapter, \ Lighting, ATX power and industrial power applications.

Description of Change (To) :
New Datasheet Description:

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as Audio, Laptop adapter, Lighting, ATX power and industrial power applications.

Reason for Change:

In description for product on page 1 of datasheet, removing sentence "In addition, internal gate-source ESD diode allows to withstand over 2kV HBM surge stress"

Correction to datasheet - Incorrect statement for this product.

Affected Product(s): Please refer to the list of affected products in the addendum attached in the PCN email you received. This list is based on an analysis of your company's procurement history.